Name :	
Roll No. :	A Pres V Execution Ind Exclored
Invigilator's Signature :	

CS/B.Tech(EE/NEW)/SEM-6/EE-605C/2013 2013 VLSI AND MICROELECTRONICS

Time Allotted : 3 Hours

Full Marks : 70

The figures in the margin indicate full marks. Candidates are required to give their answers in their own words as far as practicable.

GROUP – A

(Multiple Choice Type Questions)

1. Choose the correct alternatives for any *ten* of the following :

 $10 \times 1 = 10$

- i) VLSI stands for
 - a) Very Large Scale Integration
 - b) Very Low Scale Integration
 - c) all of these
 - d) none of these.
- ii) In LSI maximum number of transistors per chip is
 - a) 10000 b) 1000
 - c) 2000 d) none of these.

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iii) ASIC stands for



- a) Application Surface Integral Circuit
- b) Application Specific Integral Chip
- c) Application Specific Integrated Circuit
- d) All of these.
- iv) FPGA is used for
 - a) design verification b) front end design
 - c) design configuration d) none of these.
- v) PLA stands for
 - a) Programmable Logic Array
 - b) Portable Logic Array
 - c) Programmable Linear Array
 - d) all of these.
- vi) E-mos is normally
 - a) On device b) Off device
 - c) Can't be said d) all false.

vii) CMOS inverter requires minimum

- a) 2 transistors b) 4 transistors
 - c) all of these d) none of these.
- viii) VHDL is a
 - a) language b) hardware
 - c) PLA d) none of these.



GROUP – B

(Short Answer Type Questions)

	Answer any <i>three</i> of the following.	$3 \times 5 = 15$
2.	Draw NOR and NAND gates using CMOS.	$2 \times 2\frac{1}{2}$

3

- 3. Write the advantages of VLSI technology.
- 4. Sketch Y = (A + B + C).D
- 5. Sketch a stick diagram of 3-input NAND gate.

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GROUP – C



Answer any *three* of the following. $3 \times 15 = 45$

- 6. a) Draw an inverter circuit using CMOS.
 - b) Design a circuit using PAL to implement the following function :

 $F_{1} = xyz + x'y'$ $F_{2} = w'F_{1}' + wxy'z$

- c) Write a short note on FPGA. 3 + 7 + 5
- 7. a) Write a short note on *y*-chart.
 - b) Sketch a stick diagram of Y = (A + B + C).D.
 - c) Describe working principle of Enhancement MOSFET.

5 + 5 + 5

8. a) Write a VHDL programme for Full Adder.

- b) Write a VHDL program for X-OR gate.
- c) Write a short note on photo-lithography. 5 + 5 + 5
- 9. Write short notes on any *three* of the following : 3×5
 - a) PLA
 - b) Ion-implantation
 - c) ASIC
 - d) Depletion MOSFET.

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